







2N3969 N-Channel JFET

Features

- InterFET N0016H Geometry
- Low Noise: 5 nV/VHz Typical
- Low Input Capacitance: 3.5pF Typical
- · RoHS Compliant
- SMT, TH, and Bare Die Package options.

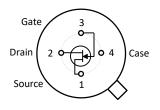
Applications

- · Audio Amplifiers
- · Small Signal Amplifier
- · High Impedance Pre-Amplifier

Description

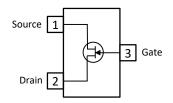
The -30V InterFET 2N3969 is targeted for sensitive amplifier stages with gate leakages typically less than 10pA at room temperatures. The TO-72 package is hermetically sealed and suitable for military applications.

TO-72 Bottom View





SOT23 Top View





Product Summary

	Parameters	2N3969 Min	2N3969A Min	Unit		
BV _{GSS}	Gate to Source Breakdown Voltage	-30	-30	V		
I _{DSS}	Drain to Source Saturation Current	0.4	0.4	mA		
$V_{GS(off)}$	Gate to Source Cutoff Voltage	-1.7 (Max)	-1.7 (Max)	V		
GFS	Forward Transconductance	1.3	1.3	mS		

Ordering Information Custom Part and Binning Options Available

Custom Part and Billing Options Available						
Part Number	Description	Case	Packaging			
2N3969	Through-Hole	TO-72	Bulk			
SMP3969	Surface Mount	SOT23	Bulk			
	7" Tape and Reel: Max 3,000 Pieces		Minimum 1,000 Pieces			
SMP3969TR	13" Tape and Reel: Max 9,000 Pieces	SOT23	Tape and Reel			
2N3969COT	Chip Orientated Tray (COT Waffle Pack)	COT	400/Waffle Pack			
2N3969CFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack			



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.









Electrical Characteristics

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

	Parameters	Value	Unit
V_{RGS}	Reverse Gate Source and Gate Drain Voltage	-50	V
I _{FG}	Continuous Forward Gate Current	50	mA
PD	Continuous Device Power Dissipation	300	mW
Р	Power Derating	2	mW/°C
TJ	Operating Junction Temperature	-55 to 125	°C
T _{STG}	Storage Temperature	-65 to 175	°C

Static Characteristics (@ TA = 25°C, Unless otherwise specified)

			2N3969		2N3969A		
	Parameters	Conditions	Min	Max	Min	Max	Unit
V _{(BR)GSS}	Gate to Source Breakdown Voltage	V _{DS} = 0V, I _G = -1μA	-30		-30		V
Igss	Gate to Source Reverse Current	V _{GS} = -20V, V _{DS} = 0V		-1.0		-1.0	nA
V _{GS(OFF)}	Gate to Source Cutoff Voltage	V _{DS} = 20V, I _D = 1nA		-1.7		-1.7	٧
I _{DSS}	Drain to Source Saturation Current	$V_{GS} = 0V$, $V_{DS} = 20V$ (Pulsed)	0.4	2.0	0.4	2.0	mA

Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

			2N3969		2N3969A		
	Parameters	Conditions	Min	Max	Min	Max	Unit
G _{FS}	Forward Transconductance	V _{DS} = 20V, I _G = -1μA	1.3		1.3		mS
Ciss	Input Capacitance	V _{DS} = 20V, V _{GS} = 0V		5.0		5.0	pF
Crss	Reverse Transfer Capacitance	V _{DS} = 20V, V _{GS} = 0V		1.3		1.3	pF



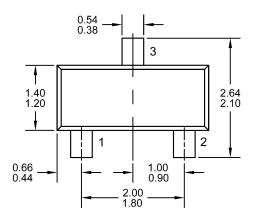


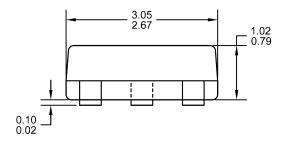




SOT23 (TO-236AB) Mechanical and Layout Data

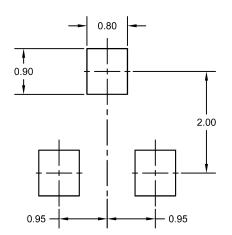
Package Outline Data





- 0.15 0.09 0.61 0.45 0.27 0.13
- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.12 grams
- 3. Molded plastic case UL 94V-0 rated
- For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
- Bulk product is shipped in standard ESD shipping material
- 6. Refer to JEDEC standards for additional information.

Suggested Pad Layout



- 1. All linear dimensions are in millimeters.
- 2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.



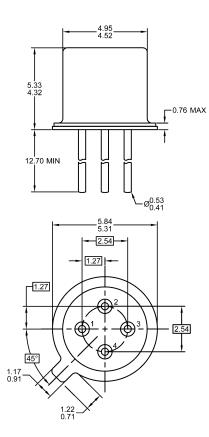






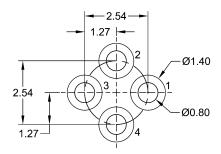
TO-72 Mechanical and Layout Data

Package Outline Data



- 1. All linear dimensions are in millimeters.
- Four leaded device. Not all leads are shown in drawing views.
- 3. Package weight approximately 0.31 grams
- Bulk product is shipped in standard ESD shipping material
- 5. Refer to JEDEC standards for additional information.

Suggested Through-Hole Layout



- 1. All linear dimensions are in millimeters.
- The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.